



40V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C			
-40V	$13m\Omega$ @ $V_{GS} = -10V$	-10.3A			
-40 V	$18m\Omega @ V_{GS} = -4.5V$	-8.8A			

Features and Benefits

- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies 33% of the Board Area Occupied by SO-8, Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

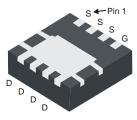
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Reverse Polarity Protection
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.072 grams (Approximate)

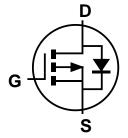
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Top View



Equivalent Circuit

Ordering Information (Note 5)

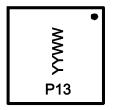
Part Number	Case	Packaging
DMP4013LFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMP4013LFGQ-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8



P13= Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	-40	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Prain Current (Note 7) V 40V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-10.3 -8.3	А
Continuous Drain Current (Note 7) V _{GS} = -10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	-13.7 -11	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-80	Α		
Maximum Continuous Body Diode Forward Current (Is	-2.6	Α		
Avalanche Current, L = 0.1mH	I _{AS}	-34	Α		
Avalanche Energy, L = 0.1mH	Eas	58	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		P _D	1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	123	°C/W
The mai Nesistance, sunction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	69	
Total Power Dissipation (Note 7)		P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	D	60	°C/W
Themai Resistance, sunction to Ambient (Note 1)	t<10s	$R_{\theta JA}$	34	
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	3.3	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

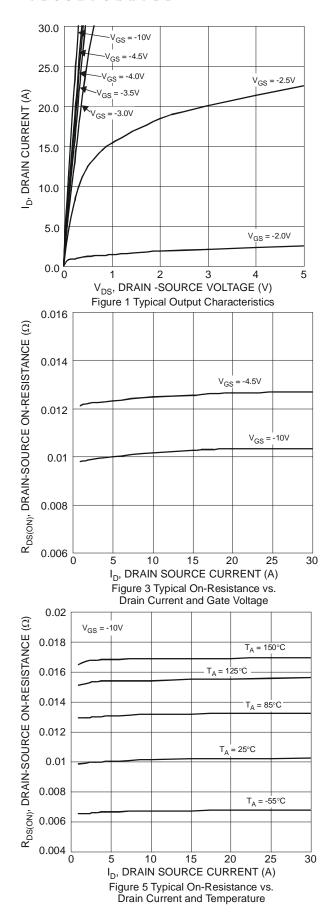
Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		-40	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C		_	_	-1	μA	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-1	_	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	9.4	13	mΩ	$V_{GS} = -10V, I_D = -10A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	12.3	18	11122	$V_{GS} = -4.5V, I_{D} = -8A$	
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A	
DYNAMIC CHARACTERISTICS (Note 9)			•			•	
Input Capacitance	C _{iss}	-	3,426	_	pF		
Output Capacitance	Coss	_	283	_	pF	$V_{DS} = -20V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	Crss	_	235	_	pF	11 = 1101712	
Gate Resistance	Rg	-	4.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	32.5	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	68.6	_	nC	1,,	
Gate-Source Charge	Qgs	_	8.2	_	nC	$V_{DS} = -20V, I_{D} = -10A$	
Gate-Drain Charge	Q_{gd}		9.9	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	1	5.3	_	ns		
Turn-On Rise Time	t _R	1	20	_	ns	$V_{DD} = -20V, V_{GEN} = -10V,$ $R_G = 3\Omega, I_D = -10A$	
Turn-Off Delay Time	t _{D(OFF)}	-	126	_	ns		
Turn-Off Fall Time	t _F		83	_	ns		
Body Diode Reverse Recovery Time	t _{RR}		19.5	_	ns	I _F = -10A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}	1	9.8	_	nC		

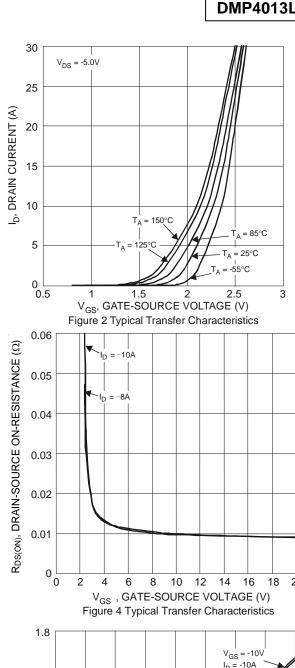
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6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.







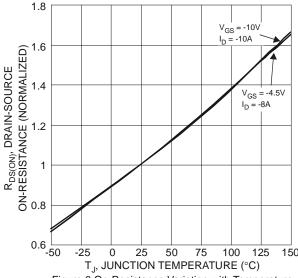
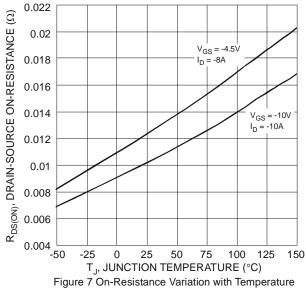
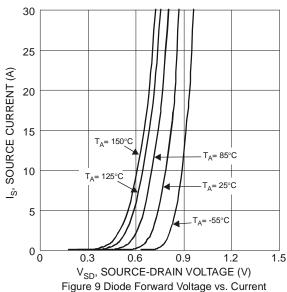
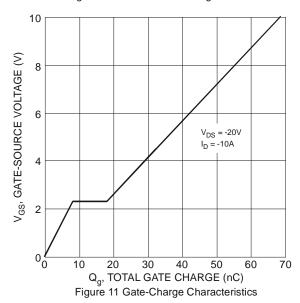


Figure 6 On-Resistance Variation with Temperature









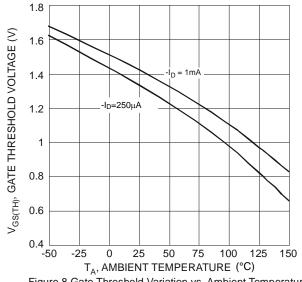
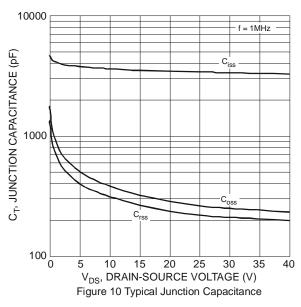
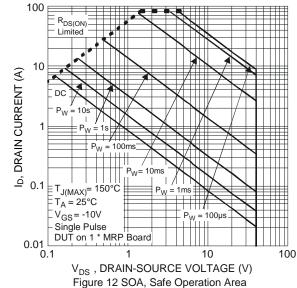
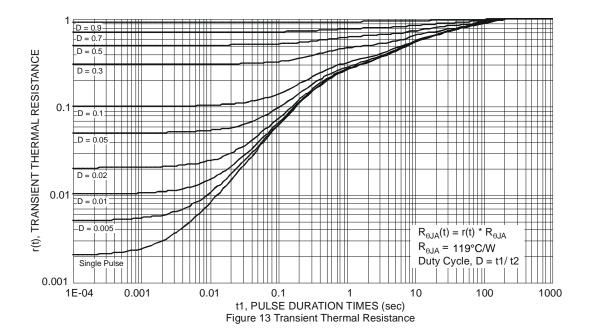


Figure 8 Gate Threshold Variation vs. Ambient Temperature







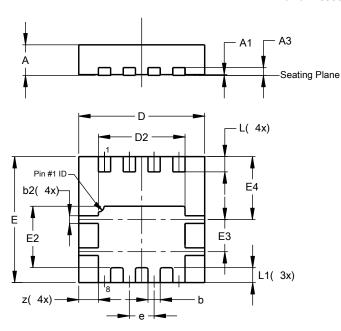




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

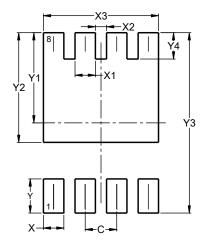


PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
А3	1	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3 25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	-	-	0.65			
L	0.35	0.45	0.40			
L1	_	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
Х3	2.370			
Υ	0.700			
Y1	1.850			
Y2	2.250			
Y3	3.700			
Y4	0.540			



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